



flowDual E2 SiC

1200 V / 8 mΩ

Topology features

- Temperature sensor
- Half Bridge

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al₂O₃
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Extra features

- Equivalent: FF6MR12W2M1H_B11

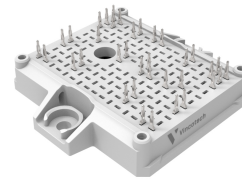
Target applications

- Charging Stations
- Energy Storage Systems
- Power Supply
- Solar Inverters
- Welding & Cutting

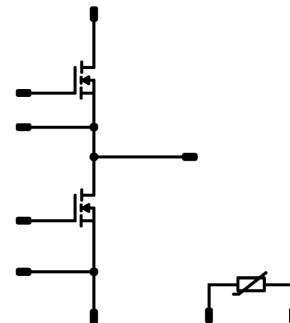
Types

- 10-EY122PA008ME-LU38F08T

flow E2 12 mm housing



Schematic





Vincotech

10-EY122PA008ME-LU38F08T
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Half-Bridge Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	151	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	480	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	271	W
Gate-source voltage	V_{GSS}		-4 / 15	V
		dynamic	-8 / 19	
Maximum Junction Temperature	T_{jmax}		175	°C

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Creepage distance			>12,7	mm
Clearance			9,34	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Half-Bridge Switch

Static

Drain-source on-state resistance	$r_{DS(on)}$		15		160	25 125 150	5,6	8,65 11,31 12,56	10,4 ⁽¹⁾	mΩ
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$			0,046	25	1,8	2,5	3,6	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		40	1000	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25		4	76	μA
Internal gate resistance	r_g							0,425		Ω
Gate charge	Q_g		-4/15	800	160	25		472		nC
Short-circuit input capacitance	C_{iss}	$f = 100$ kHz	0	1000	0	25		13428		pF
Short-circuit output capacitance	C_{oss}							516		
Reverse transfer capacitance	C_{rss}							32		
Diode forward voltage	V_{SD}		0		80	25		4,6		V

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,35		K/W
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Vincotech

10-EY122PA008ME-LU38F08T
datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit				
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max						
Dynamic														
Turn-on delay time	$t_{d(on)}$	$R_{gon} = 4 \Omega$ $R_{goff} = 4 \Omega$	-4/15	600	160	25		47,44		ns				
						125		41,82						
						150		41						
Rise time	t_r									25		27,73		ns
						125		23,55						
						150		22,54						
Turn-off delay time	$t_{d(off)}$									25		97,94		ns
						125		108,16						
						150		111,04						
Fall time	t_f									25		11,84		ns
						125		12,1						
						150		12,3						
Turn-on energy (per pulse)	E_{on}	$Q_{rFWD}=0,73 \mu C$ $Q_{rFWD}=2,01 \mu C$ $Q_{rFWD}=2,56 \mu C$				25		3,84		mWs				
						125		3,75						
						150		3,86						
Turn-off energy (per pulse)	E_{off}					25		1,39		mWs				
						125		1,34						
						150		1,34						
Peak recovery current	I_{RRM}					25		65,62		A				
						125		100,98						
						150		115,2						
Reverse recovery time	t_{rr}					25		19,97		ns				
						125		33,87						
						150		38,28						
Recovered charge	Q_r	$di/dt=7877 A/\mu s$ $di/dt=7976 A/\mu s$ $di/dt=9066 A/\mu s$				25		0,73		μC				
						125		2,01						
						150		2,56						
Reverse recovered energy	E_{rec}					25		0,076		mWs				
						125		0,381						
						150		0,533						
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25		10743,09		A/ μs				
						125		7016,04						
						150		7213,8						



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit	
		V_{GS} [V]	V_{GE} [V]	V_{DS} [V]	V_{CE} [V]	V_F [V]	I_D [A]	I_C [A]	I_F [A]		T_j [°C]

Thermistor

Static

Rated resistance	R					25		5		kΩ
Deviation of R100	$A_{R/R}$	$R_{100} = 493 \Omega$				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 2 \%$						3375		K
B-value	$B_{(25/100)}$	Tol. $\pm 2 \%$						3437		K
Vincotech Thermistor Reference									K	

⁽¹⁾ Value at chip level

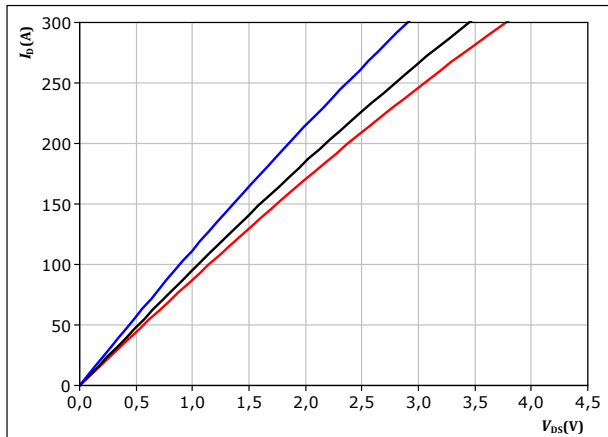
⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



Half-Bridge Switch Characteristics

figure 1. MOSFET

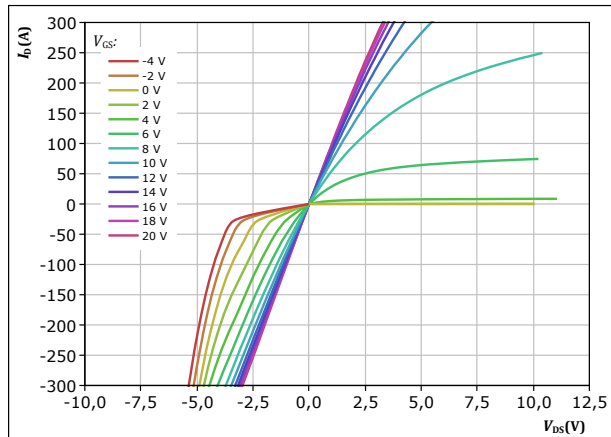
Typical output characteristics
 $I_D = f(V_{DS})$



$t_p = 250 \mu s$
 $V_{GS} = 14 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 2. MOSFET

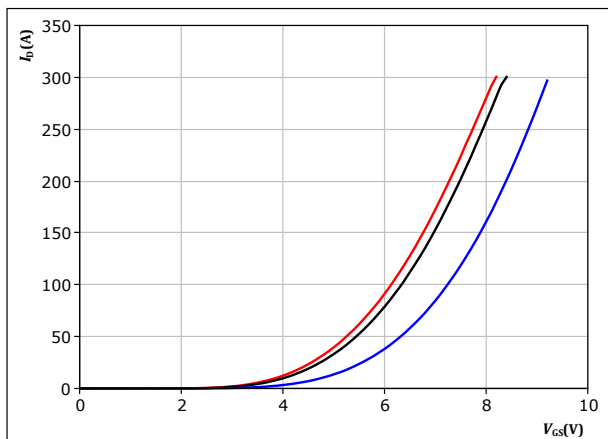
Typical output characteristics
 $I_D = f(V_{DS})$



$t_p = 250 \mu s$
 $T_j = 150 \text{ °C}$
 V_{GS} from -4 V to 20 V in steps of 2 V

figure 3. MOSFET

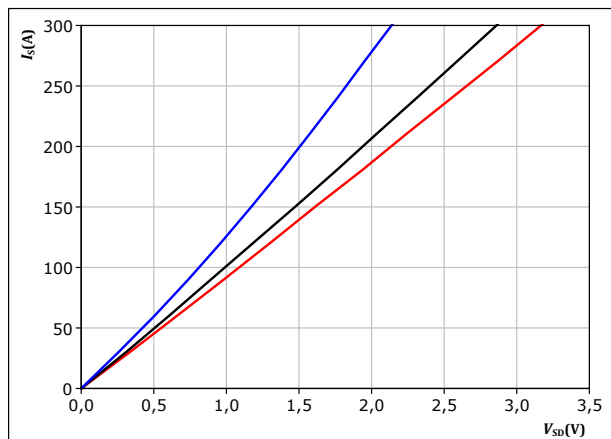
Typical transfer characteristics
 $I_D = f(V_{GS})$



$t_p = 250 \mu s$
 $V_{DS} = 10 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 4. MOSFET

Typical reverse drain current characteristics
 $I_{SD} = f(V_{SD})$



$t_p = 250 \mu s$
 $V_{GS} = 14 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

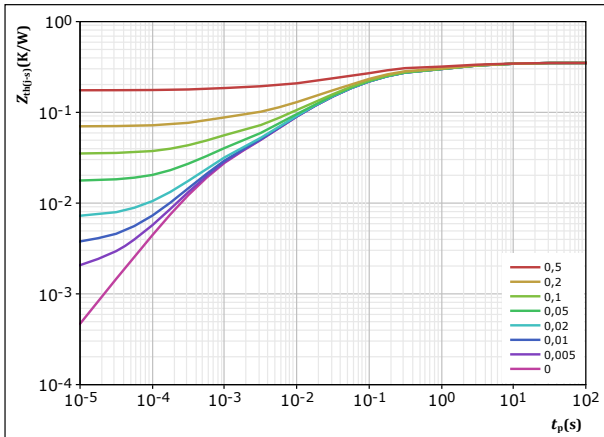


Half-Bridge Switch Characteristics

figure 5. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-c)} = f(t_p)$$



$$D = \frac{t_p}{T}$$

$$R_{th(j-c)} = 0,35 \text{ K/W}$$

MOSFET thermal model values

R (K/W)	τ (s)
2,38E-02	7,80E+00
6,28E-02	1,30E+00
1,63E-01	8,44E-02
7,75E-02	1,05E-02
2,34E-02	6,20E-04

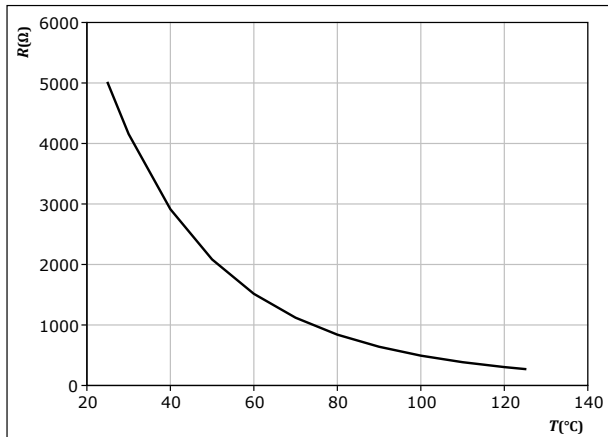


Thermistor Characteristics

figure 6. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$

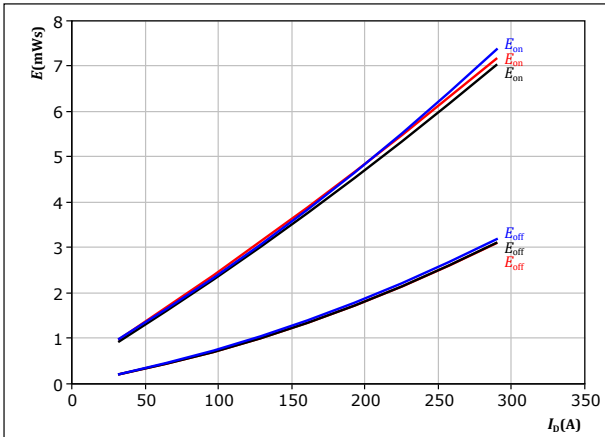




Half-Bridge Switching Characteristics

figure 7. MOSFET

Typical switching energy losses as a function of drain current
 $E = f(I_D)$

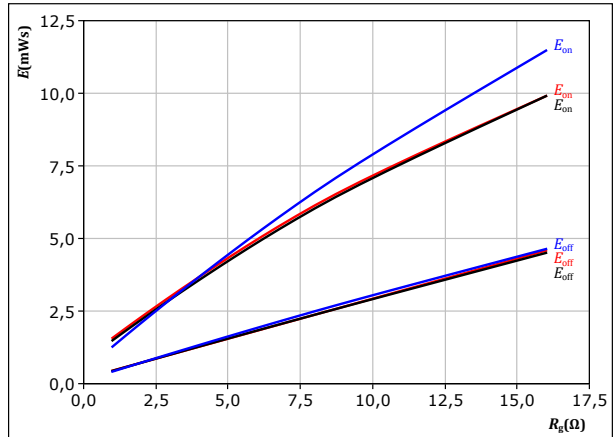


With an inductive load at

$V_{DS} = 600$ V	$T_j = 25$ °C
$V_{GS} = -4/15$ V	$T_j = 125$ °C
$R_{gon} = 4$ Ω	$T_j = 150$ °C
$R_{goff} = 4$ Ω	

figure 8. MOSFET

Typical switching energy losses as a function of MOSFET turn on gate resistor
 $E = f(R_g)$

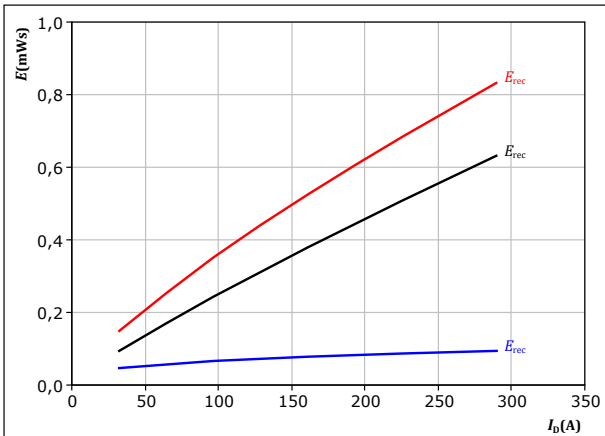


With an inductive load at

$V_{DS} = 600$ V	$T_j = 25$ °C
$V_{GS} = -4/15$ V	$T_j = 125$ °C
$I_D = 160$ A	$T_j = 150$ °C

figure 9. MOSFET

Typical reverse recovered energy loss as a function of drain current
 $E_{rec} = f(I_D)$

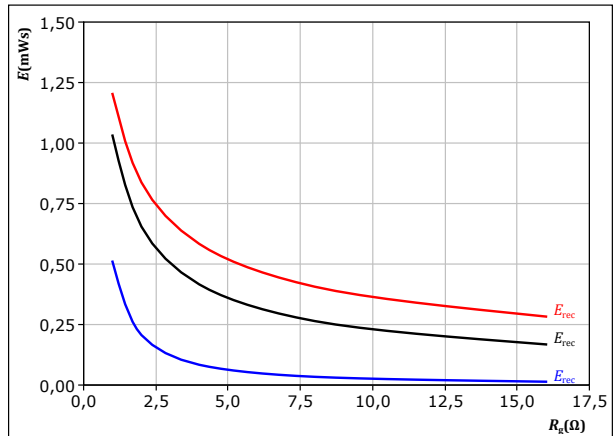


With an inductive load at

$V_{DS} = 600$ V	$T_j = 25$ °C
$V_{GS} = -4/15$ V	$T_j = 125$ °C
$R_{gon} = 4$ Ω	$T_j = 150$ °C

figure 10. MOSFET

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at

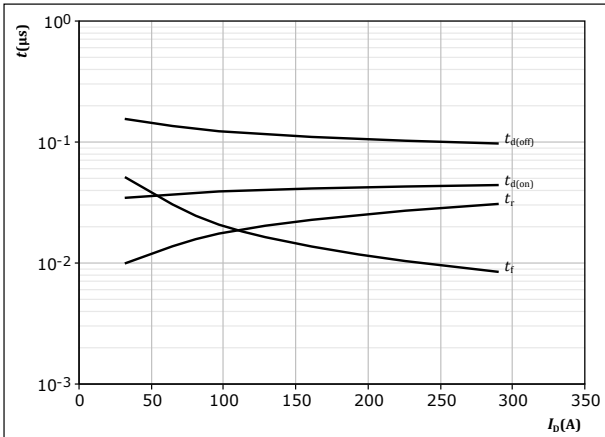
$V_{DS} = 600$ V	$T_j = 25$ °C
$V_{GS} = -4/15$ V	$T_j = 125$ °C
$I_D = 160$ A	$T_j = 150$ °C



Half-Bridge Switching Characteristics

figure 11. MOSFET

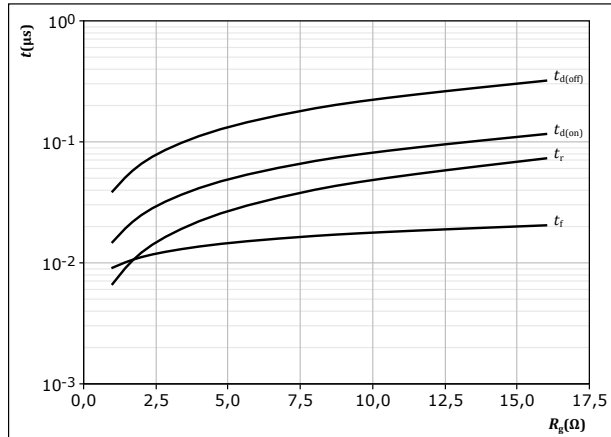
Typical switching times as a function of drain current
 $t = f(I_D)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{g(on)} = 4 \text{ } \Omega$
 $R_{g(off)} = 4 \text{ } \Omega$

figure 12. MOSFET

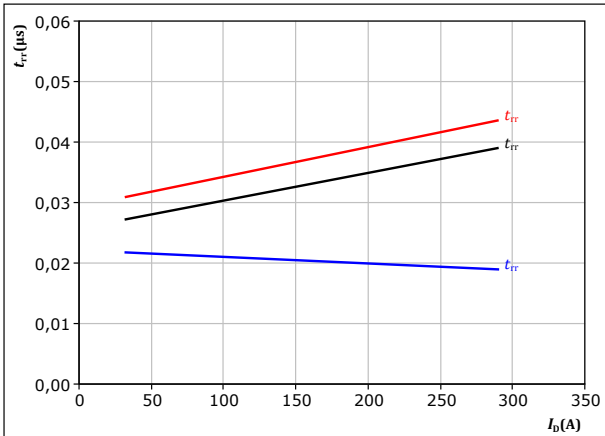
Typical switching times as a function of MOSFET turn on gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 160 \text{ A}$

figure 13. MOSFET

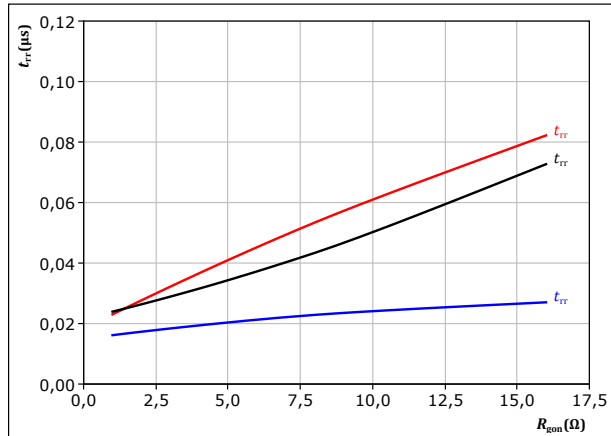
Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{g(on)} = 4 \text{ } \Omega$
 T_j : — 25 °C
— 125 °C
— 150 °C

figure 14. MOSFET

Typical reverse recovery time as a function of MOSFET turn on gate resistor
 $t_{rr} = f(R_{g(on)})$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 160 \text{ A}$
 T_j : — 25 °C
— 125 °C
— 150 °C

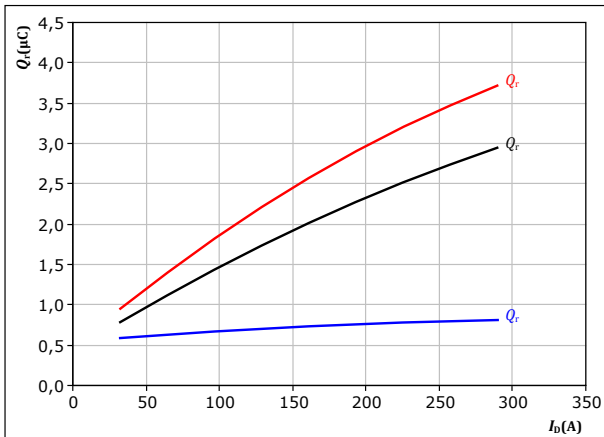


Half-Bridge Switching Characteristics

figure 15. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$

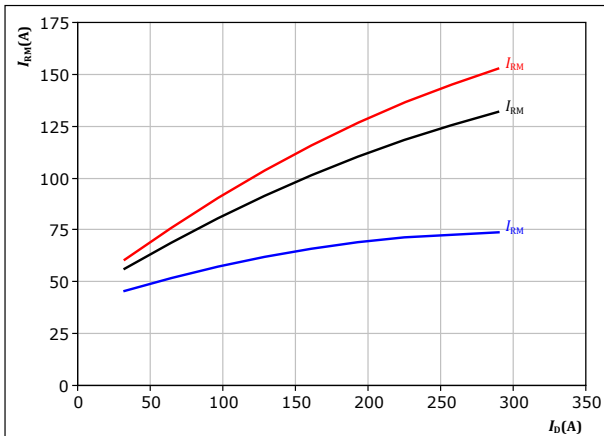


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gon} = 4$ Ω
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 17. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$

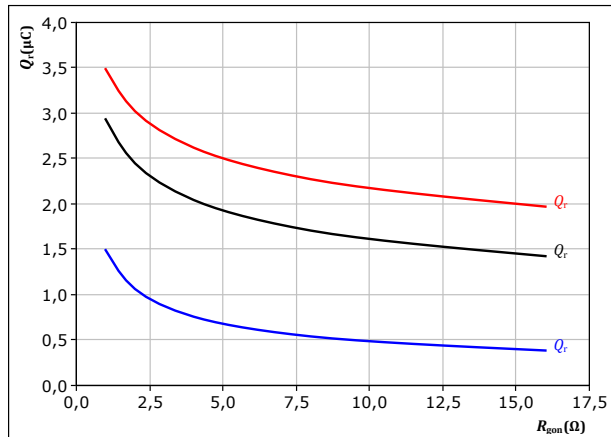


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gon} = 4$ Ω
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 16. MOSFET

Typical recovered charge as a function of MOSFET turn on gate resistor

$$Q_r = f(R_{gon})$$

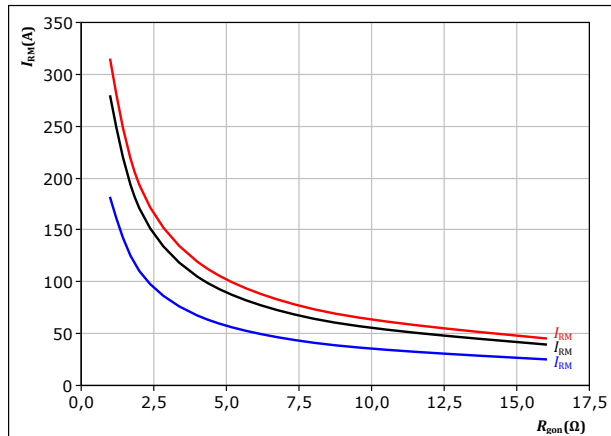


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 160$ A
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 18. MOSFET

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$$I_{RM} = f(R_{gon})$$



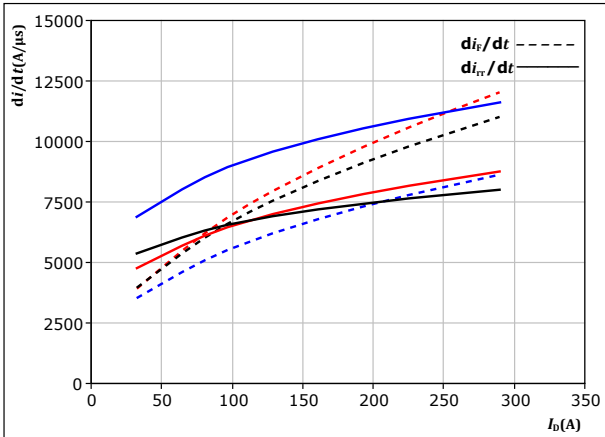
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 160$ A
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)



Half-Bridge Switching Characteristics

figure 19. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_{rr}/dt = f(I_D)$

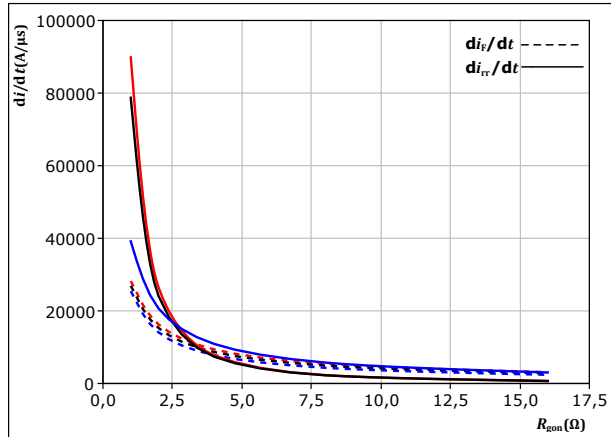


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{g(on)} = 4$ Ω

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 20. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{g(on)})$

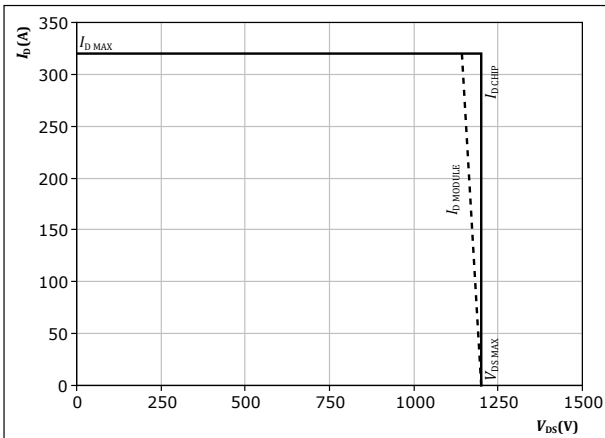


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 160$ A

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 21. MOSFET

Reverse bias safe operating area
 $I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{g(on)} = 4$ Ω
 $R_{g(off)} = 4$ Ω



Half-Bridge Switching Definitions

figure 22. MOSFET

Turn-off Switching Waveforms & definition of t_{doff} t_{Eoff} (t_{Eoff} = integrating time for E_{off})

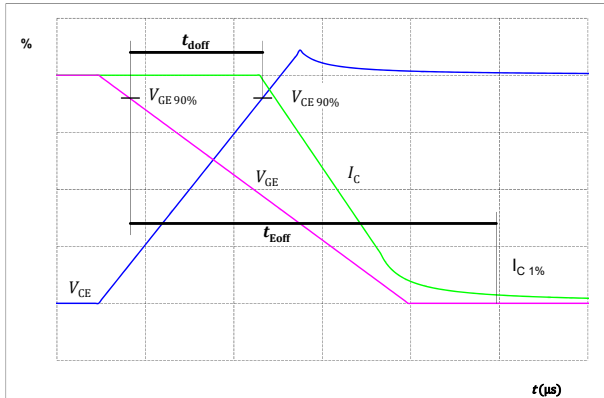


figure 23. MOSFET

Turn-on Switching Waveforms & definition of t_{don} t_{Eon} (t_{Eon} = integrating time for E_{on})

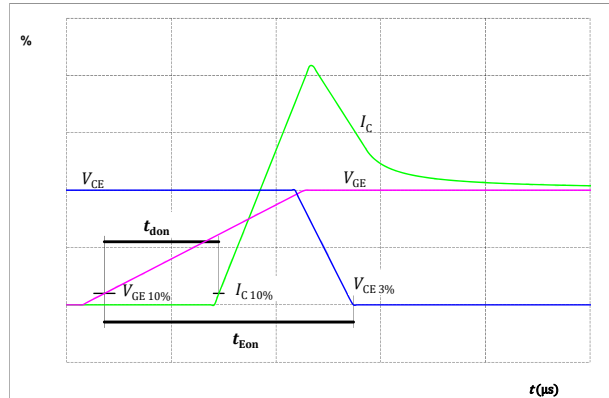


figure 24. MOSFET

Turn-off Switching Waveforms & definition of t_f

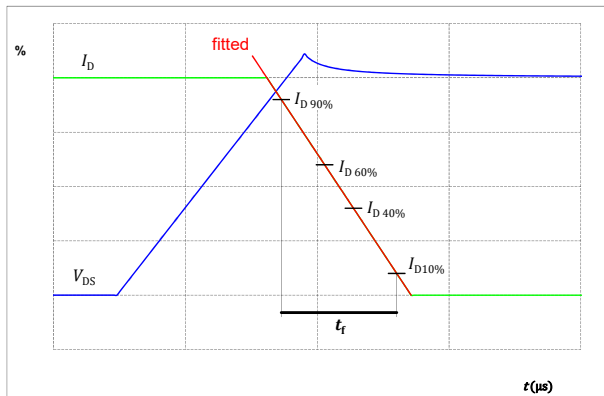
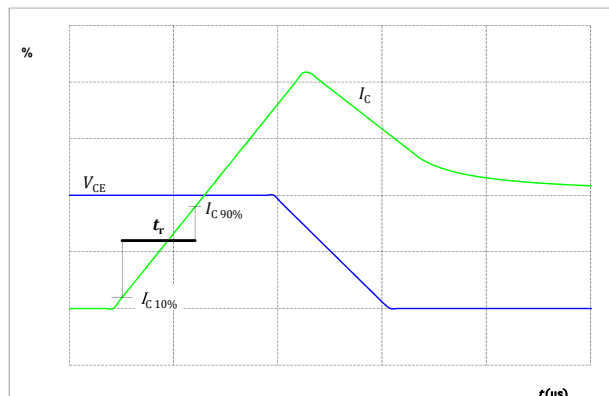


figure 25. MOSFET

Turn-on Switching Waveforms & definition of t_r





Half-Bridge Switching Definitions

figure 26. FWD

Turn-off Switching Waveforms & definition of t_{tr}

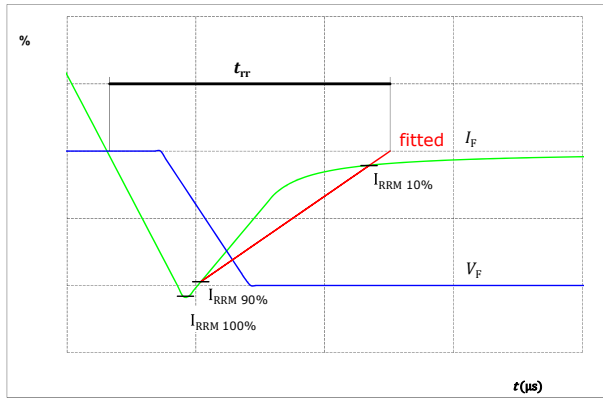


figure 27. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

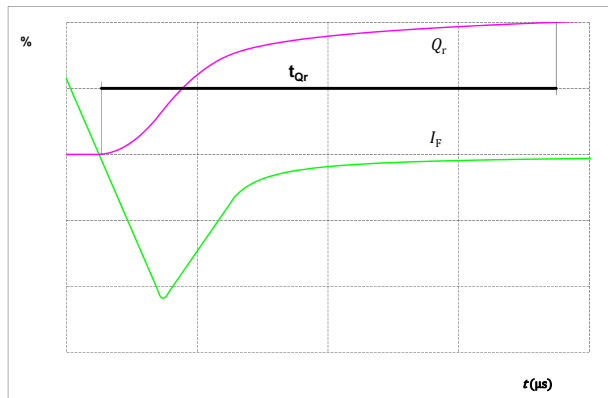
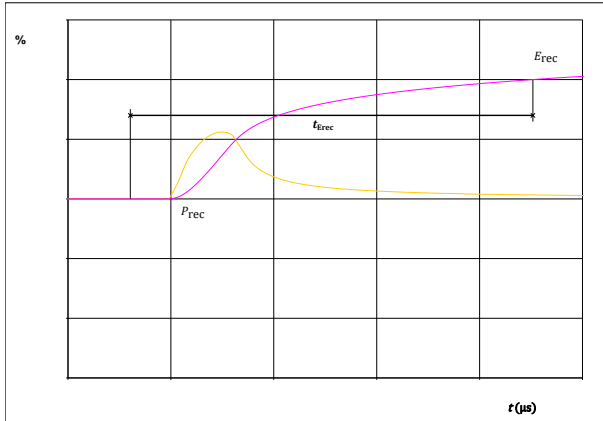


figure 28. FWD

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



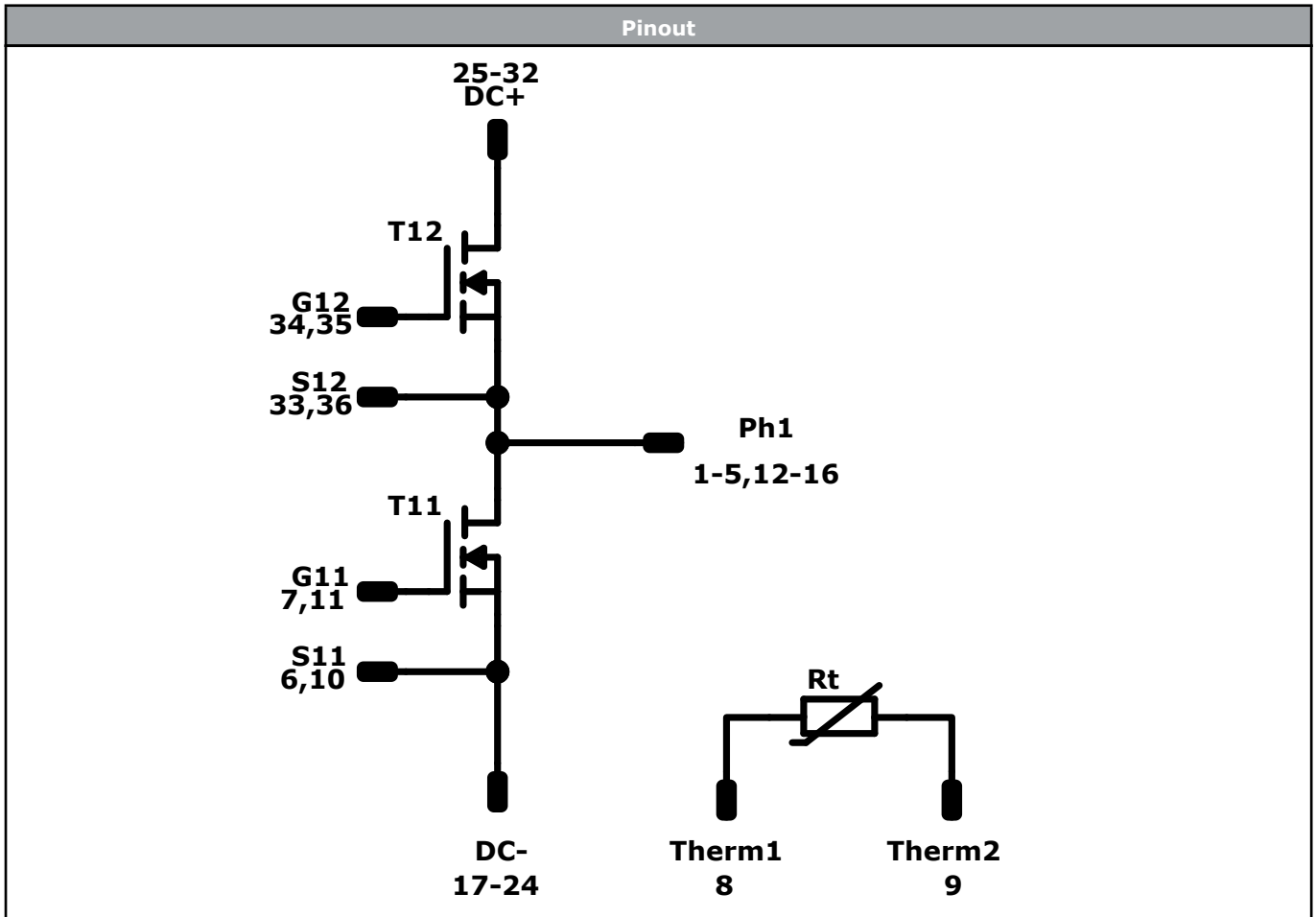


Vincotech

Ordering Code	
Version	Ordering Code
Without thermal paste	10-EY122PA008ME-LU38F08T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EY122PA008ME-LU38F08T-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-EY122PA008ME-LU38F08T-/3/

Marking						
	Text	Name NN-NNNNNNNNNNNNNNNN- TTTTTTTVV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL	Serial SSSS
	Datamatrix	Type&Ver TTTTTTTVV	Lot number LLLLL	Serial SSSS	Date code WWYY	

Outline			
Pin table [mm]			
Pin	X	Y	Function
1	25,6	48	Ph1
2	28,8	48	Ph1
3	32	48	Ph1
4	28,8	44,8	Ph1
5	32	44,8	Ph1
6	28,8	35,2	S11
7	32	35,2	G11
8	32	28,8	Therm1
9	32	25,6	Therm2
10	28,8	12,8	S11
11	32	12,8	G11
12	28,8	3,2	Ph1
13	32	3,2	Ph1
14	32	0	Ph1
15	28,8	0	Ph1
16	25,6	0	Ph1
17	19,2	6,4	DC-
18	16	9,6	DC-
19	16	16	DC-
20	16	19,2	DC-
21	19,2	19,2	DC-
22	16	28,8	DC-
23	19,2	28,8	DC-
24	19,2	41,6	DC-
25	12,8	48	DC+
26	9,6	48	DC+
27	6,4	35,2	DC+
28	3,2	35,2	DC+
29	6,4	12,8	DC+
30	3,2	12,8	DC+
31	12,8	0	DC+
32	9,6	0	DC+
33	0	0	S12
34	0	3,2	G12
35	0	44,8	G12
36	0	48	S12



Identification					
ID	Component	Voltage	Current	Function	Comment
T11, T12	MOSFET	1200 V	8 mΩ	Half-Bridge Switch	
Rt	Thermistor			Thermistor	



Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow</i> E2 packages see vincotech.com website.

Package data
Package data for <i>flow</i> E2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}=175^{\circ}C$ and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.



Document No.:	Date:	Modification:	Pages
10-EY122PA008ME-LU38F08T-D2-14	12 Apr. 2024	Update of Characteristic Values	

DISCLAIMER

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.